



# STPS6030CW

## LOW DROP POWER SCHOTTKY RECTIFIER

### MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 30 A
$V_{RRM}$	30 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	0.45 V

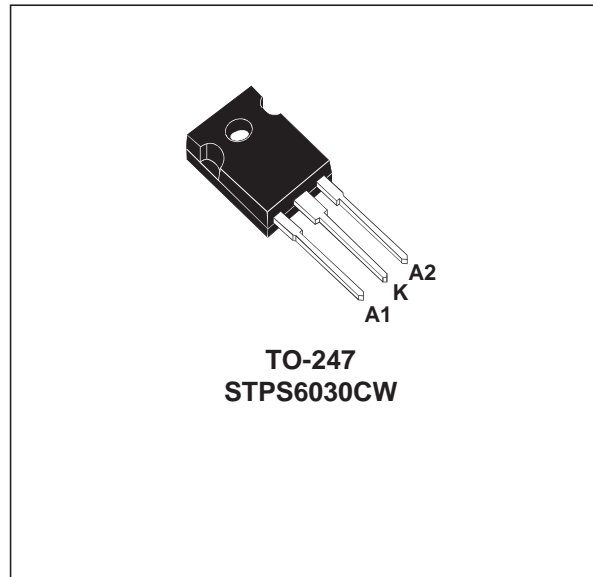
### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP FOR HIGHER EFFICIENCY
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Dual Schottky rectifier suited for switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-247, this device is intended for use in low voltage high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	30	V
$I_{F(RMS)}$	RMS forward current	45	A
$I_{F(AV)}$	Average forward current	$T_c = 130^\circ\text{C}$ $\delta = 0.5$ Per diode: 30 Per device: 60	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	300 A
$I_{RRM}$	Peak repetitive reverse current	$t_p = 2 \mu\text{s}$ square $F = 1\text{kHz}$	2 A
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	7700 W
$T_{stg}$	Storage temperature range	- 65 to + 150	°C
$T_j$	Maximum operating junction temperature *	150	°C
$dV/dt$	Critical rate of rise of reverse voltage (rated $V_R$ , $T_j = 25^\circ\text{C}$ )	10000	V/ $\mu\text{s}$

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.9	°C/W
		Total	0.6	
$R_{th(c)}$		Coupling	0.3	°C/W

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_J = 25^\circ\text{C}$	$V_R = V_{RRM}$		0.7	1.5	mA
		$T_J = 125^\circ\text{C}$			200	400	
$V_F^*$	Forward voltage drop	$T_J = 25^\circ\text{C}$	$I_F = 30\text{ A}$		0.46	0.52	V
		$T_J = 125^\circ\text{C}$	$I_F = 30\text{ A}$		0.39	0.45	
		$T_J = 25^\circ\text{C}$	$I_F = 60\text{ A}$		0.58	0.65	
		$T_J = 125^\circ\text{C}$	$I_F = 60\text{ A}$		0.56	0.63	

Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.27 \times I_{F(AV)} + 0.006 I_{F(RMS)}^2$$

Fig. 1: Conduction losses versus average current.

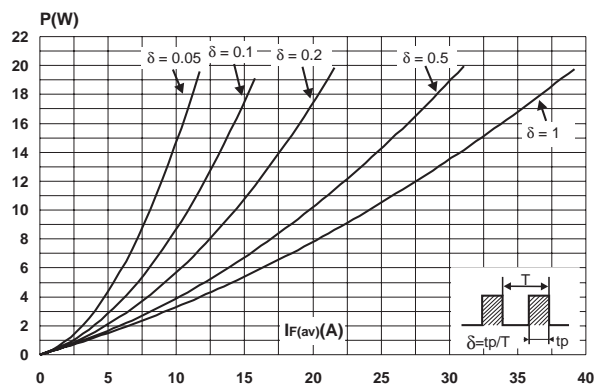


Fig. 3: Normalized avalanche power derating versus pulse duration.

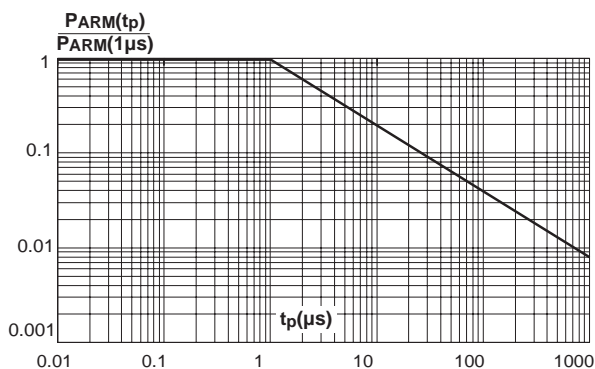


Fig. 2: Average forward current versus ambient temperature (delta = 0.5).

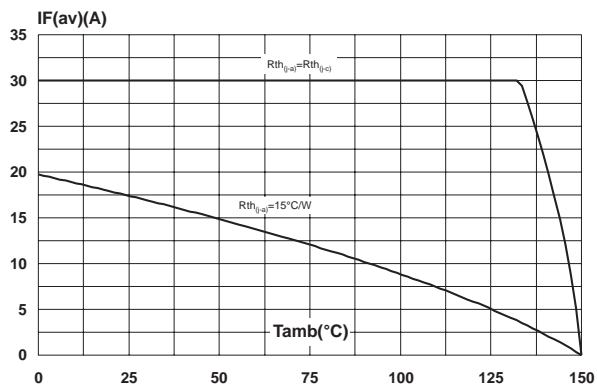
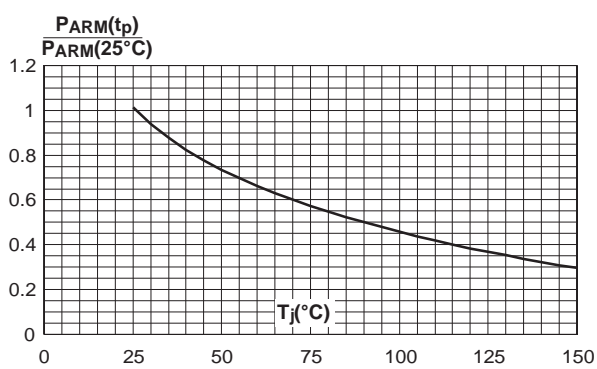
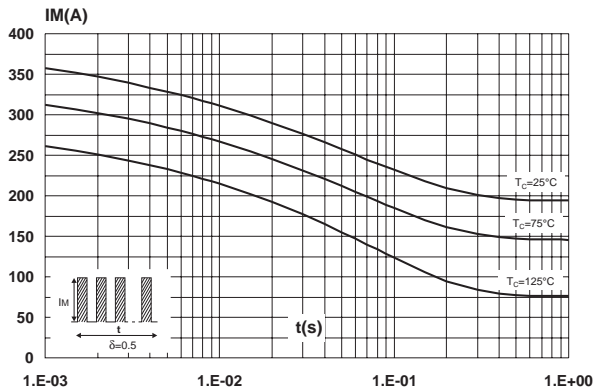


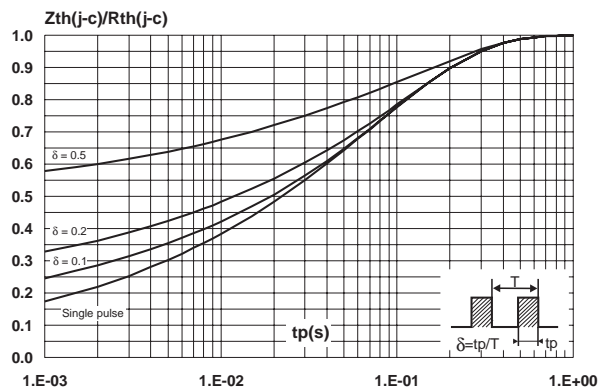
Fig. 4: Normalized avalanche power derating versus junction temperature.



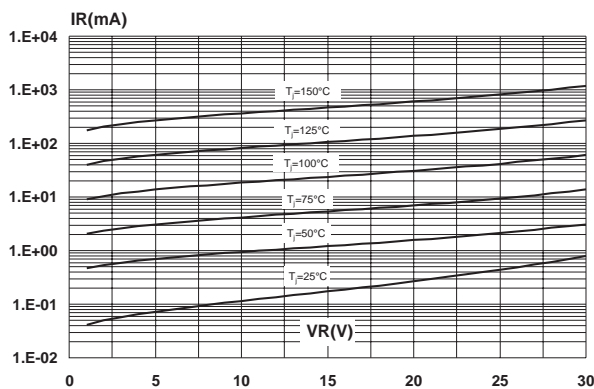
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values).



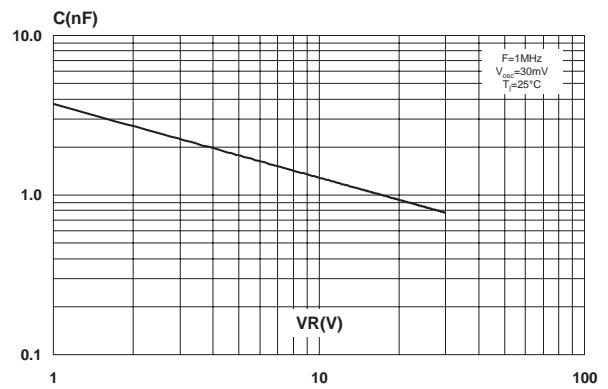
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration.



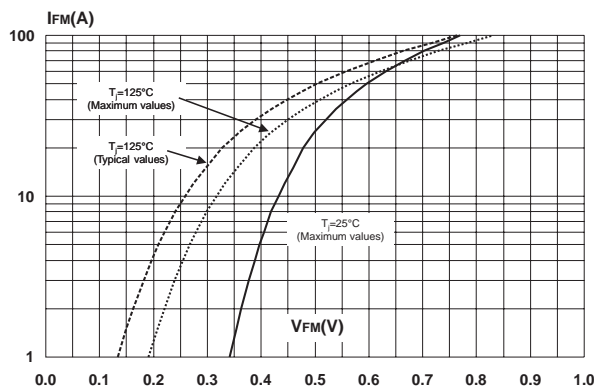
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values).



**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).

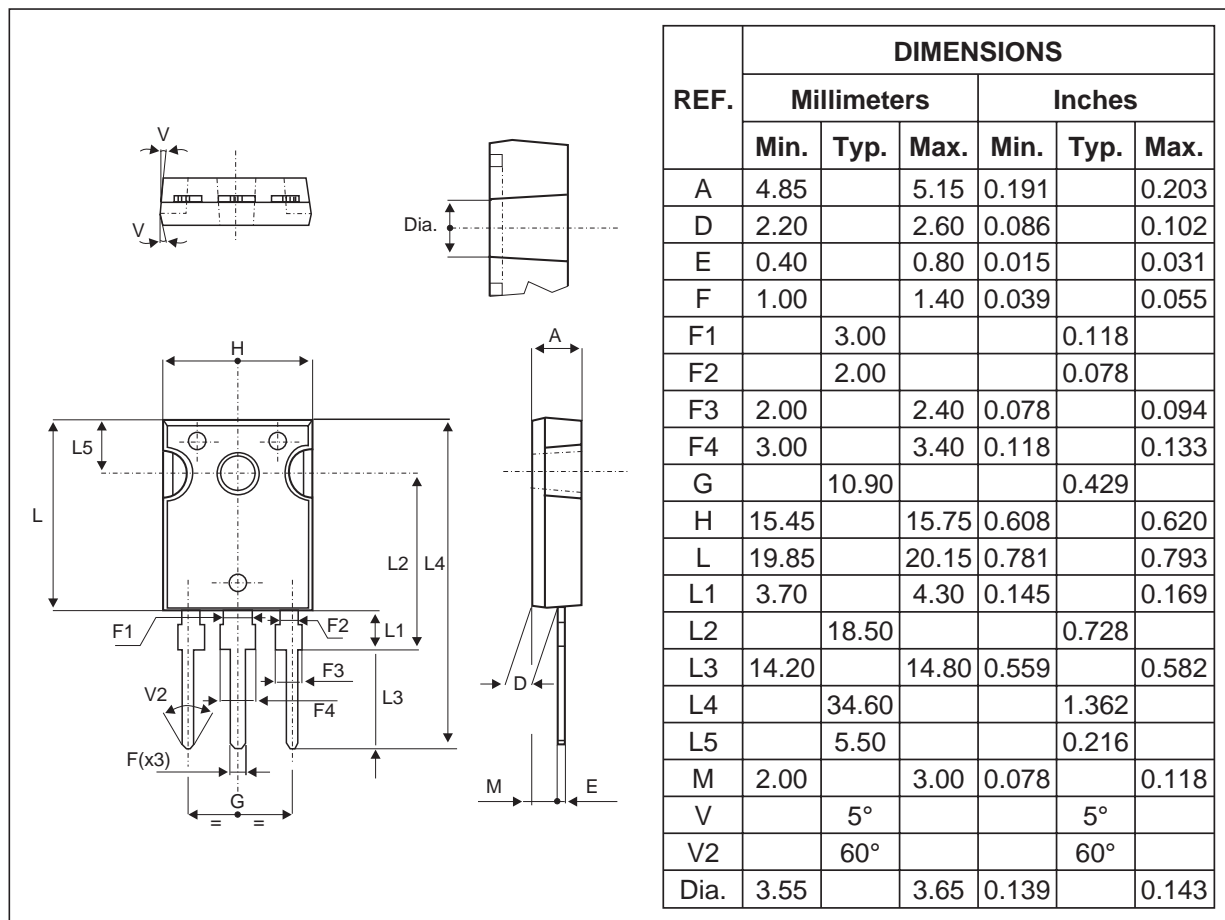


**Fig. 9:** Forward voltage drop versus forward current.



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## PACKAGE MECHANICAL DATA TO-247



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS6030CW	STPS6030CW	TO-247	4.4 g	30	Tube

- EPOXY MEETS UL94,V0

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